# RENESAS

# LOW COST 27 MHZ 3.3 VOLT VCXO

# ICS722

## Description

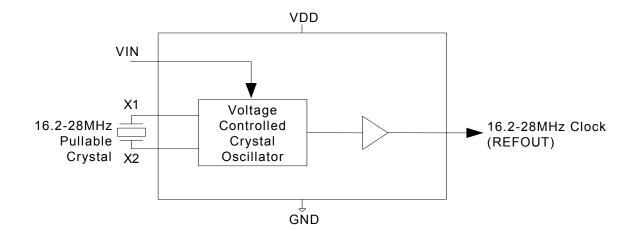
The ICS722 is a low cost, low-jitter, high-performance 3.3 volt VCXO designed to replace expensive discrete VCXOs modules. The on-chip Voltage Controlled Crystal Oscillator accepts a 0 to 3.3 V input voltage to cause the output clocks to vary by over  $\pm 100$  ppm. Using IDT's patented VCXO techniques, the device uses an inexpensive external pullable crystal in the range of 16.2 to 28 MHz to produce a VCXO output clock at that same frequency.

The frequency of the on-chip VCXO is adjusted by an external control voltage input into pin VIN. Because VIN is a high-impedance input, it can be driven directly from an PWM RC integrator circuit. Frequency output increases with VIN voltage input. The usable range of VIN is 0 to 3.3 V.

IDT manufactures the largest variety of Set-Top Box and multimedia clock synthesizers for all applications. Consult IDT to eliminate VCXOs, crystals, and oscillators from your board.

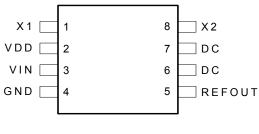
## **Features**

- Packaged in 8-pin SOIC (Pb free, RoHS compliant)
- Operational frequency range of 16.2 MHz to 28 MHz
- Uses an inexpensive external crystal
- On-chip patented VCXO with pull range of 230 ppm (minimum)
- VCXO tuning voltage of 0 to 3.3 V
- Operating voltage of 3.3 V
- 12 mA output drive capability at TTL levels
- Advanced, low-power, sub-micron CMOS process



# **Block Diagram**

# **Pin Assignment**



ICS722

8-Pin (150 mil) SOIC

# **Pin Descriptions**

Pin Number	Pin Name	Pin Type	Pin Description
1	XI	Input	Crystal connection. Connect to the external pullable crystal.
2	VDD	Power	Connect to +3.3 V (0.01µf decoupling capacitor recommended).
3	VIN	Input	Voltage input to VCXO. Zero to 3.3 V signal which controls the VCXO frequency.
4	GND	Power	Connect to ground.
5	REFOUT	Output	VCXO CMOS level clock output matches the nominal frequency of the crystal.
6	DC	—	Do not connect anything to this pin.
7	DC	—	Do not connect anything to this pin.
8	X2	Input	Crystal connection. Connect to a external pullable crystal.

# **External Component Selection**

The ICS722 requires a minimum number of external components for proper operation.

### **Decoupling Capacitors**

A decoupling capacitor of  $0.01\mu$ F should be connected between VDD and GND on pins 2 and 4 as close to the ICS722 as possible. For optimum device performance, the decoupling capacitor should be mounted on the component side of the PCB. Avoid the use of vias in the decoupling circuit.

### **Series Termination Resistor**

When the PCB trace between the clock output and the load is over 1 inch, series termination should be used. To series terminate a  $50\Omega$  trace (a commonly used trace impedance), place a  $33\Omega$  resistor in series with the clock line, as close to the clock output pin as possible. The nominal impedance of the clock output is  $20\Omega$ 

## **Quartz Crystal**

The ICS722 VCXO function consists of the external crystal and the integrated VCXO oscillator circuit. To assure the best system performance (frequency pull range) and reliability, a crystal device with the recommended parameters (shown below) must be used, and the layout guidelines discussed in the following section shown must be followed.

The oscillation frequency of a quartz crystal is determined by its "cut" and by the load capacitors connected to it. The ICS722 incorporates on-chip variable load capacitors that "pull" (change) the frequency of the crystal. The crystal specified for use with the ICS722 is designed to have zero frequency error when the total of on-chip + stray capacitance is 14 pF.

#### **Recommended Crystal Parameters:**

Initial Accuracy at 25°C	±20 ppm
Temperature Stability	±30 ppm
Aging	±20 ppm
Load Capacitance	14 pf
Shunt Capacitance, C0	7 pF Max
C0/C1 Ratio	250 Max
Equivalent Series Resistance	$35 \Omega \text{Max}$

The external crystal must be connected as close to the chip

as possible and should be on the same side of the PCB as the ICS722. There should be no via's between the crystal pins and the X1 and X2 device pins. There should be no signal traces underneath or close to the crystal. See application note MAN05.

## **Crystal Tuning Load Capacitors**

The crystal traces should include pads for small fixed capacitors, one between X1 and ground, and another between X2 and ground. Stuffing of these capacitors on the PCB is optional. The need for these capacitors is determined at system prototype evaluation, and is influenced by the particular crystal used (manufacture and frequency) and by PCB layout. The typical required capacitor value is 1 to 4 pF.

The procedure for determining the value of these capacitors can be found in application note MAN05.

## **Absolute Maximum Ratings**

Stresses above the ratings listed below can cause permanent damage to the ICS722. These ratings, which are standard values for IDT commercially rated parts, are stress ratings only. Functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods can affect product reliability. Electrical parameters are guaranteed only over the recommended operating temperature range.

Item	Rating
Supply Voltage, VDD	7 V
All Inputs and Outputs	-0.5 V to VDD+0.5 V
Ambient Operating Temperature	0 to +70° C
Storage Temperature	-65 to +150° C
Soldering Temperature	260° C

## **Recommended Operation Conditions**

Parameter	Min.	Тур.	Max.	Units
Ambient Operating Temperature	0	-	+70	°C
Power Supply Voltage (measured in respect to GND)	+3.15		+3.45	V
Reference crystal parameters	Refer to page 3			•

## **DC Electrical Characteristics**

VDD=3.3 V ±5%	, Ambient temperature	0 to +70° C, unle	ss stated otherwise
---------------	-----------------------	-------------------	---------------------

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Operating Voltage	VDD		3.145		3.465	V
Output High Voltage	V <sub>OH</sub>	I <sub>OH</sub> = -12 mA	2.4			V
Output Low Voltage	V <sub>OL</sub>	I <sub>OL</sub> = 12 mA			0.4	V
Output High Voltage (CMOS Level)	V <sub>OH</sub>	I <sub>OH</sub> = -4 mA	VDD-0.4			V
Operating Supply Current	IDD	No load		6		mA
Short Circuit Current	I <sub>OS</sub>			±50		mA
VIN, VCXO Control Voltage	V <sub>IA</sub>		0		3.3	V

# **AC Electrical Characteristics**

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Output Frequency	F <sub>O</sub>		16.2		28	MHz
Crystal Pullability	F <sub>P</sub>	0V <u>&lt;</u> VIN <u>&lt;</u> 3.3 V, Note 1	<u>+</u> 115			ppm
VCXO Gain		VIN = VDD/2 <u>+</u> 1 V, Note 1		120		ppm/V
Output Rise Time	t <sub>OR</sub>	0.8 to 2.0 V, C <sub>L</sub> =15 pF			1.5	ns
Output Fall Time	t <sub>OF</sub>	2.0 to 0.8 V, C <sub>L</sub> =15 pF			1.5	ns
Output Clock Duty Cycle	t <sub>D</sub>	Measured at 1.4 V, $C_L$ =15 pF	40	50	60	%
Maximum Output Jitter, short term	tj	C <sub>L</sub> =15 pF		110		ps

VDD = 3.3 V ±5%, Ambient Temperature 0 to +70° C, unless stated otherwise

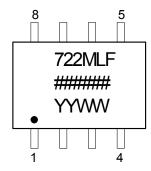
Note 1: External crystal device must conform with Pullable Crystal Specifications listed on page 3.

# **Thermal Characteristics**

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Thermal Resistance Junction to	$\theta_{JA}$	Still air		150		° C/W
Ambient	$\theta_{JA}$	1 m/s air flow		140		° C/W
	$\theta_{JA}$	3 m/s air flow		120		° C/W
Thermal Resistance Junction to Case	$\theta_{JC}$			40		° C/W

5

# **Marking Diagram**



Notes:

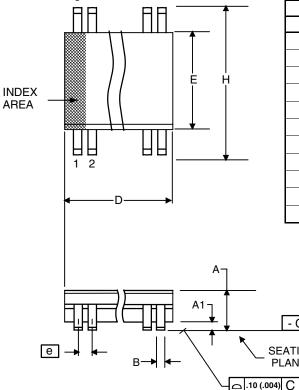
- 1. ###### is the lot number.
- 2. YYWW is the last two digits of the year and week that the part was assembled.
- 3. "LF" denotes Pb (lead) free package.
- 4. Bottom marking: (origin)
  - Origin = country of origin if not USA.

ICS722

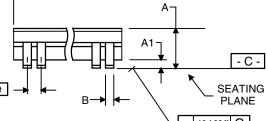
8

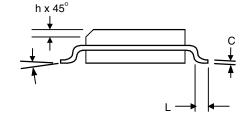
# Package Outline and Package Dimensions (8-pin SOIC)

Package dimensions are kept current with JEDEC Publication No. 95



	Millim	neters	Inc	hes	
Symbol	Min	Max	Min	Max	
A	1.35	1.75	0.0532	0.0688	
A1	1.10	0.25	0.0040	0.0098	
В	0.33	0.51	0.013	0.020	
С	0.19	0.25	0.0075	0.0098	
D	4.80	5.00	.1890	.1968	
E	3.80	4.00	0.1497	0.1574	
е	1.27	Basic	0.050 Basic		
Н	5.80	6.20	0.2284	0.2440	
h	0.25	0.50	0.010	0.020	
L	0.40	1.27	0.016	0.050	
а	<b>0</b> °	<b>8</b> °	<b>0</b> °	8°	





# **Ordering Information**

Part / Order Number	Marking	Shipping Packaging	Package	Temperature
722MLF	see page 5	Tubes	8-pin SOIC	0 to +70° C
722MLFT		Tape and Reel	8-pin SOIC	0 to +70° C

#### "LF" denotes Pb (lead) free package.

While the information presented herein has been checked for both accuracy and reliability, Integrated Device Technology (IDT) assumes no responsibility for either its use or for the infringement of any patents or other rights of third parties, which would result from its use. No other circuits, patents, or licenses are implied. This product is intended for use in normal commercial applications. Any other applications such as those requiring extended temperature range, high reliability, or other extraordinary environmental requirements are not recommended without additional processing by IDT. IDT reserves the right to change any circuitry or specifications without notice. IDT does not authorize or warrant any IDT product for use in life support devices or critical medical instruments.

vcxo

#### IMPORTANT NOTICE AND DISCLAIMER

RENESAS ELECTRONICS CORPORATION AND ITS SUBSIDIARIES ("RENESAS") PROVIDES TECHNICAL SPECIFICATIONS AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS OR IMPLIED, INCLUDING, WITHOUT LIMITATION, ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT OF THIRD-PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for developers who are designing with Renesas products. You are solely responsible for (1) selecting the appropriate products for your application, (2) designing, validating, and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. Renesas grants you permission to use these resources only to develop an application that uses Renesas products. Other reproduction or use of these resources is strictly prohibited. No license is granted to any other Renesas intellectual property or to any third-party intellectual property. Renesas disclaims responsibility for, and you will fully indemnify Renesas and its representatives against, any claims, damages, costs, losses, or liabilities arising from your use of these resources. Renesas' products are provided only subject to Renesas' Terms and Conditions of Sale or other applicable terms agreed to in writing. No use of any Renesas resources expands or otherwise alters any applicable warranties or warranty disclaimers for these products.

(Disclaimer Rev.1.01)

#### **Corporate Headquarters**

TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

#### Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners.

#### **Contact Information**

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit <u>www.renesas.com/contact-us/</u>.